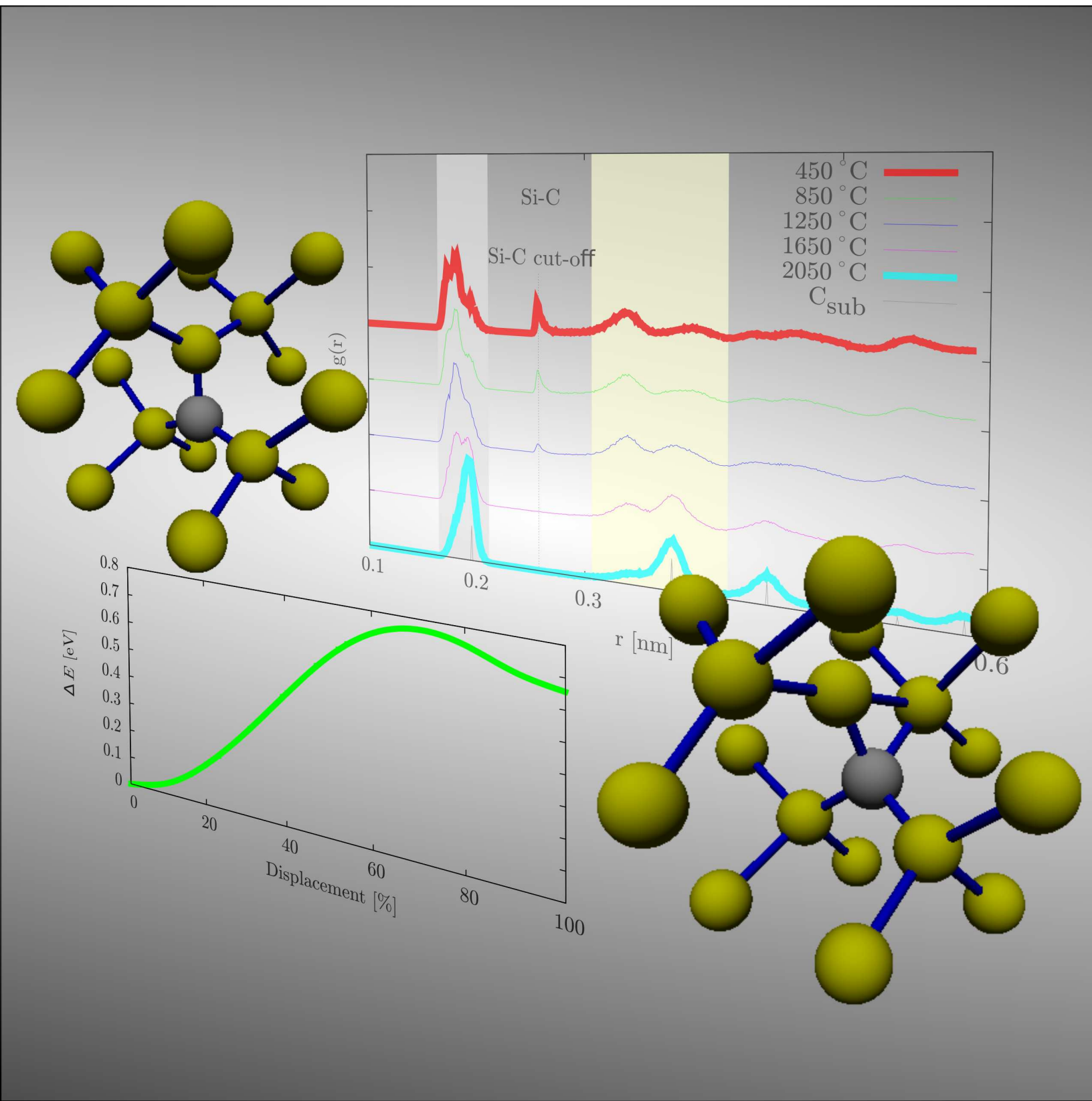
Si-C
Si-C cut-off
450 °C
850 °C
1250 °C
1650 °C
2050 °C
C_sub
g(r)
r [nm]
0.1
0.2
0.3
0.6
ΔE [eV]
Displacement [%]
0
20
40
60
80
100